

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Excellent Thermal Performance
- RoHS and Halogen-Free Compliant

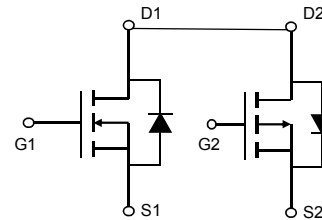
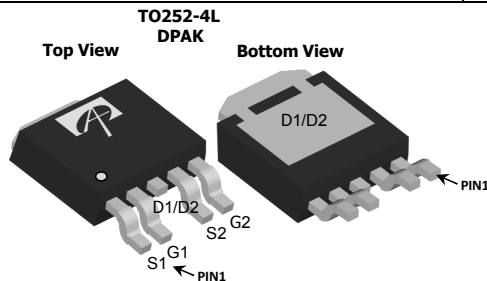
Applications

- Pch+Nch Complementary MOSFET for DC-FAN

Product Summary

| | Q1 | Q2 |
|----------------------------------|----------------|----------------|
| V_{DS} | 30V | -30V |
| I_D (at $V_{GS}=10V$) | 8A | -12A |
| $R_{DS(ON)}$ (at $V_{GS}=10V$) | < 25m Ω | < 27m Ω |
| $R_{DS(ON)}$ (at $V_{GS}=4.5V$) | < 38m Ω | < 45m Ω |

100% UIS Tested
 100% Rg Tested



| Orderable Part Number | Package Type | Form | Minimum Order Quantity |
|-----------------------|--------------|-------------|------------------------|
| AOD607A | TO-252-4L | Tape & Reel | 2500 |

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Max Q1 | Max Q2 | Units |
|--|----------------|------------|----------|------------------|
| Drain-Source Voltage | V_{DS} | 30 | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | ± 20 | V |
| Continuous Drain Current ^G | I_D | 8 | -12 | A |
| Current ^G | | 8 | -9.4 | |
| Pulsed Drain Current ^C | I_{DM} | 44 | -48 | |
| Continuous Drain Current ^G | I_{DSM} | 8 | 12 | A |
| Current ^G | | 8 | 9.5 | |
| Avalanche Current ^C | I_{AS} | 12 | -18 | A |
| Avalanche energy | E_{AS} | 7 | 16 | mJ |
| V_{DS} Spike | V_{SPIKE} | 36 | -36 | V |
| Power Dissipation ^B | P_D | 19 | 30 | W |
| | | 7.5 | 12 | |
| Power Dissipation ^A | P_{DSM} | 6.2 | 6.2 | W |
| | | 4.0 | 4.0 | |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ Q1 | Typ Q2 | Max Q1 | Max Q2 | Units |
|--|-----------------|--------|--------|--------|--------|--------------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 15 | 15 | 20 | 20 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Ambient ^{A,D} | | 40 | 40 | 50 | 50 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Case | $R_{\theta JC}$ | 5.0 | 3.2 | 6.5 | 4.2 | $^\circ\text{C/W}$ |

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|--|--|-----|--------------|----------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 30 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =30V, V _{GS} =0V T _J =55°C | | | 1 5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} =±20V | | | 100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 1.5 | 2.1 | 2.6 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} =10V, I _D =8A T _J =125°C | | 20.5 31.5 | 25 39 | mΩ |
| | | V _{GS} =4.5V, I _D =5A | | 28 | 38 | |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =8A | | 20 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.75 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current ^G | | | | 8 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =15V, f=1MHz | | 395 | | pF |
| C _{oss} | Output Capacitance | | | 67 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 41 | | pF |
| R _g | Gate resistance | f=1MHz | 0.9 | 1.8 | 2.8 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _g (10V) | Total Gate Charge | V _{GS} =10V, V _{DS} =15V, I _D =8A | | 7.2 | 15 | nC |
| Q _g (4.5V) | Total Gate Charge | | | 3.5 | 7 | nC |
| Q _{gs} | Gate Source Charge | | | 1.3 | | nC |
| Q _{gd} | Gate Drain Charge | | | 1.7 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =10V, V _{DS} =15V, R _L =1.87Ω, R _{GEN} =3Ω | | 4.5 | | ns |
| t _r | Turn-On Rise Time | | | 2.7 | | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 14.9 | | ns |
| t _f | Turn-Off Fall Time | | | 2.9 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =8A, di/dt=500A/μs | | 6.0 | | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =8A, di/dt=500A/μs | | 6.6 | | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

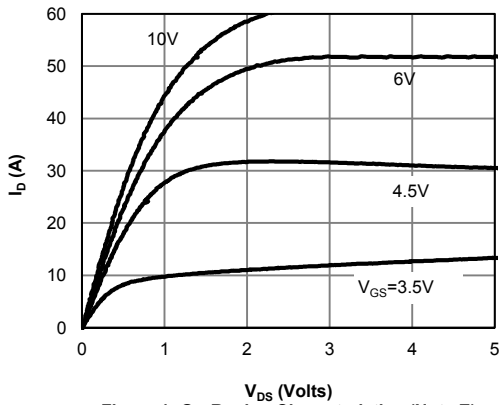


Figure 1: On-Region Characteristics (Note E)

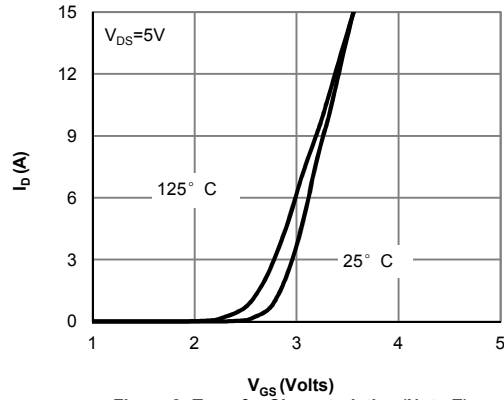


Figure 2: Transfer Characteristics (Note E)

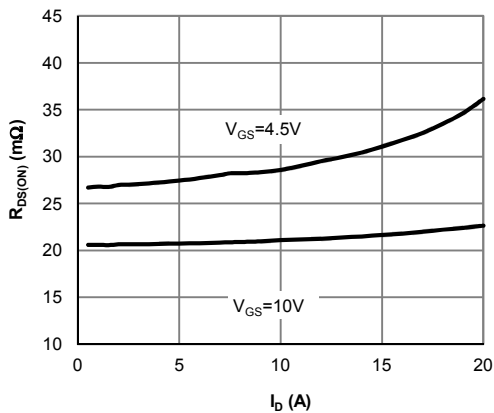


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

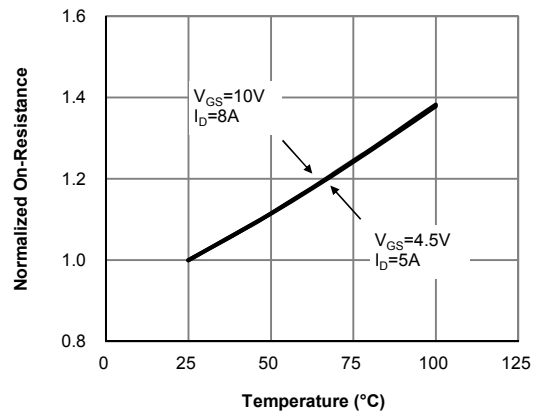


Figure 4: On-Resistance vs. Junction Temperature (Note E)

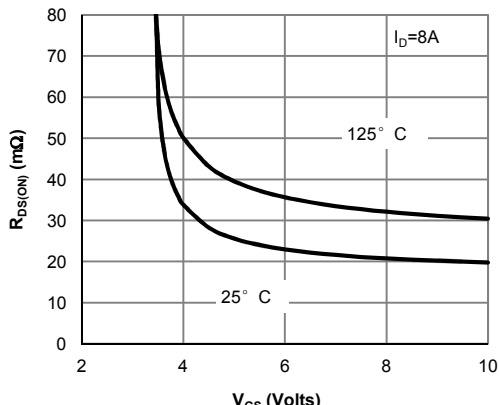


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

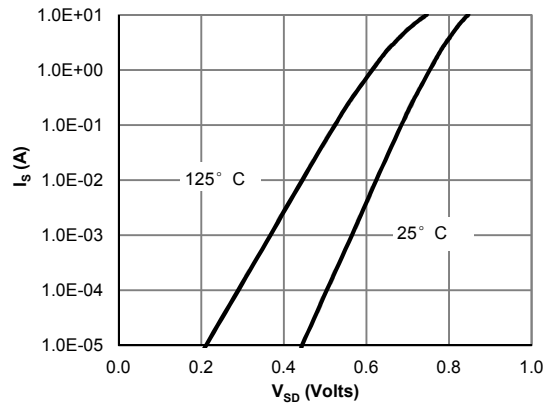


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

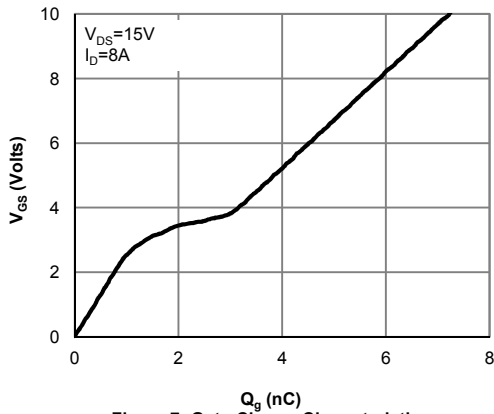


Figure 7: Gate-Charge Characteristics

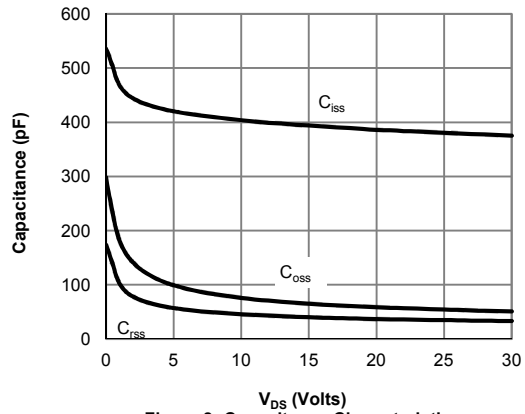


Figure 8: Capacitance Characteristics

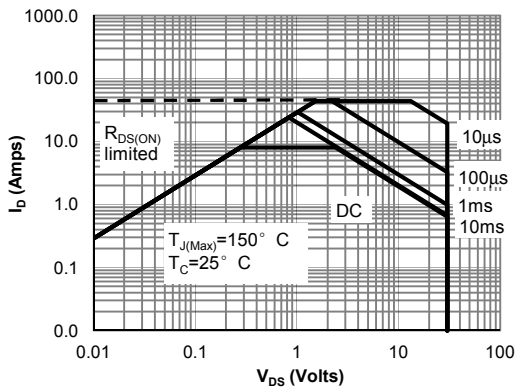


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

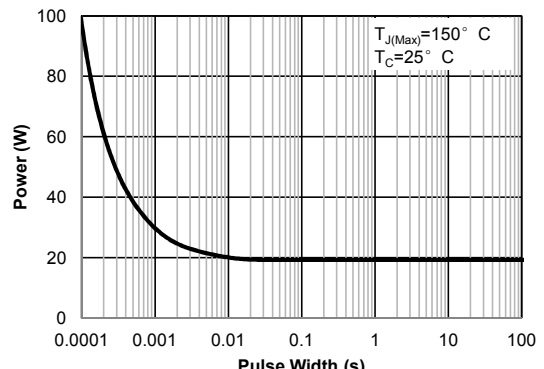


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

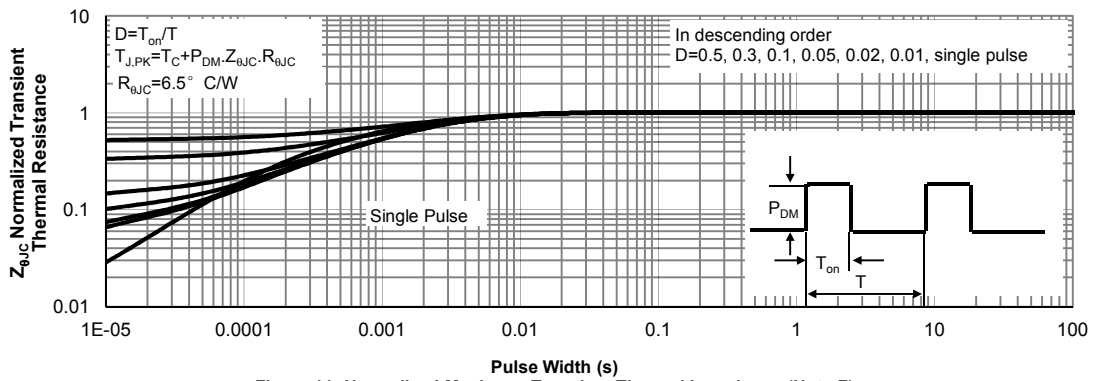


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

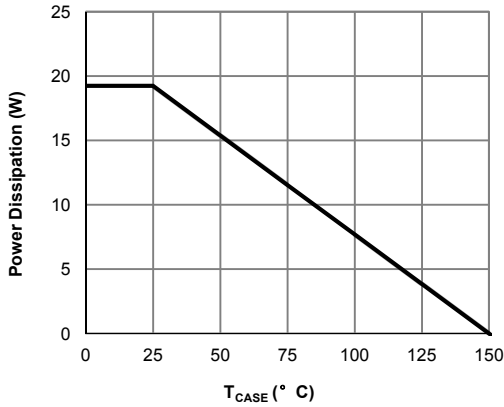


Figure 12: Power De-rating (Note F)

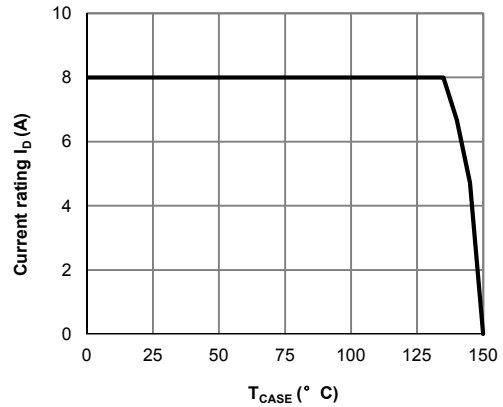


Figure 13: Current De-rating (Note F)

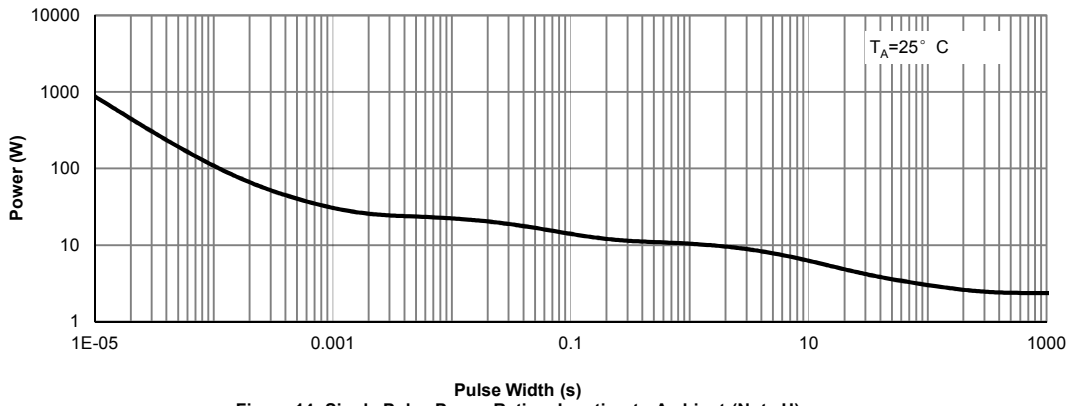


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

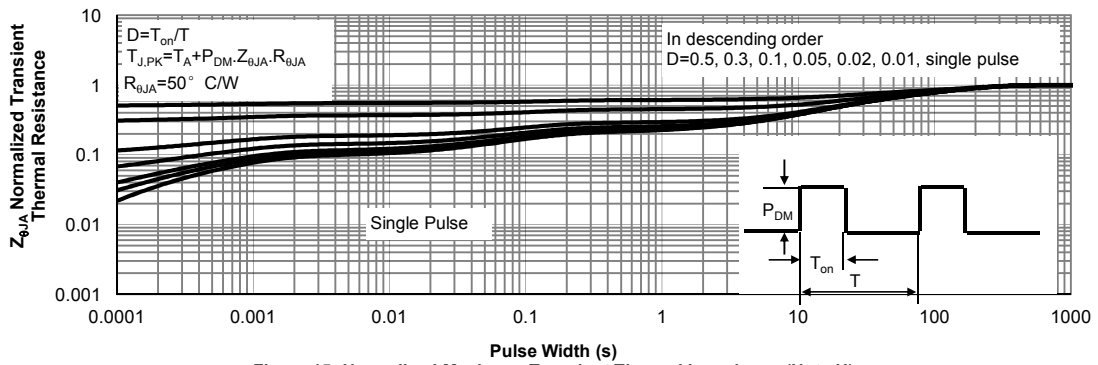


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|--|--|------|----------|----------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =-250μA, V _{GS} =0V | -30 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =-30V, V _{GS} =0V T _J =55°C | | | -1 -5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} =±20V | | | ±100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =-250μA | -1.3 | -1.85 | -2.4 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} =-10V, I _D =-12A T _J =125°C | | 22 32 | 27 40 | mΩ |
| | | V _{GS} =-4.5V, I _D =-10A | | 33 | 45 | |
| g _{FS} | Forward Transconductance | V _{DS} =-5V, I _D =-12A | | 19 | | S |
| V _{SD} | Diode Forward Voltage | I _S =-1A, V _{GS} =0V | | -0.75 | -1 | V |
| I _S | Maximum Body-Diode Continuous Current ^G | | | | 12 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =-15V, f=1MHz | | 730 | | pF |
| C _{oss} | Output Capacitance | | | 140 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 90 | | pF |
| R _g | Gate resistance | f=1MHz | | 2.1 | 5 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _g (10V) | Total Gate Charge | V _{GS} =-10V, V _{DS} =-15V, I _D =-12A | | 13.6 | 24 | nC |
| Q _g (4.5V) | Total Gate Charge | | | 6.7 | 12 | nC |
| Q _{gs} | Gate Source Charge | | | 2.5 | | nC |
| Q _{gd} | Gate Drain Charge | | | 3.2 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =-10V, V _{DS} =-15V, R _L =1.25Ω, R _{GEN} =3Ω | | 8 | | ns |
| t _r | Turn-On Rise Time | | | 6 | | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 17 | | ns |
| t _f | Turn-Off Fall Time | | | 5 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =-12A, di/dt=500A/μs | | 12 | | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =-12A, di/dt=500A/μs | | 25.5 | | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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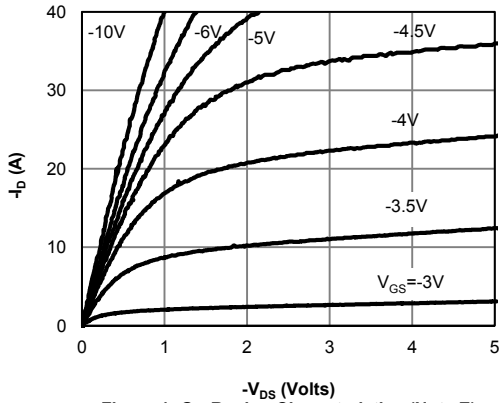


Figure 1: On-Region Characteristics (Note E)

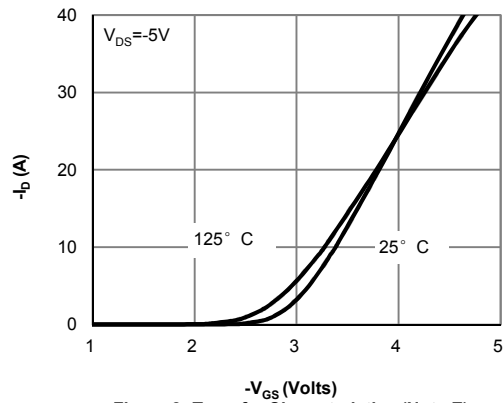


Figure 2: Transfer Characteristics (Note E)

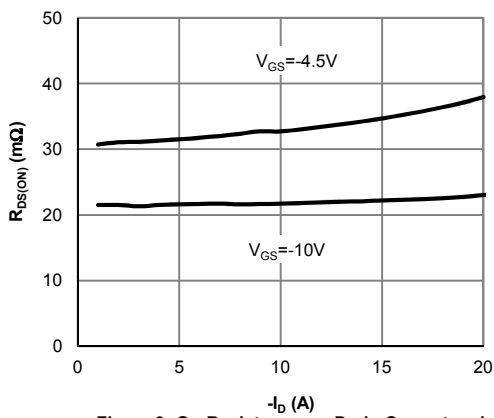


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

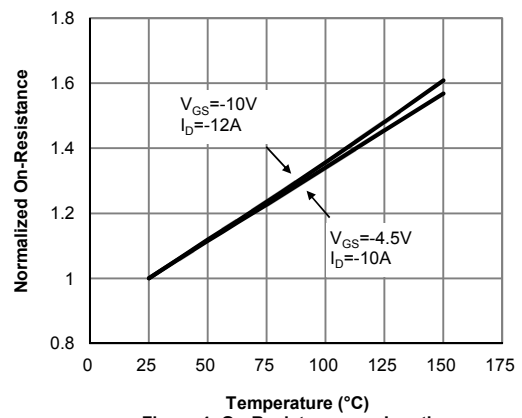


Figure 4: On-Resistance vs. Junction Temperature (Note E)

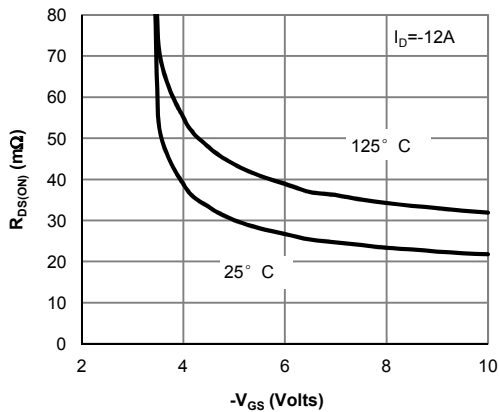


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

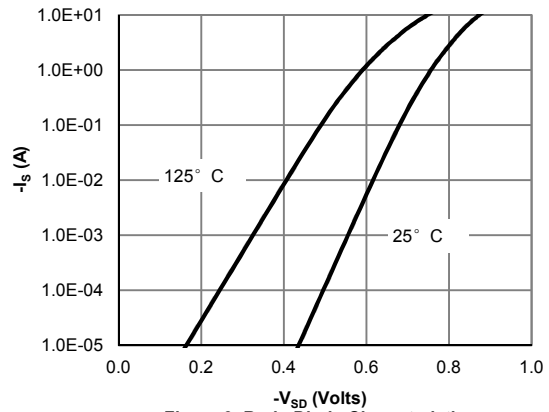


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

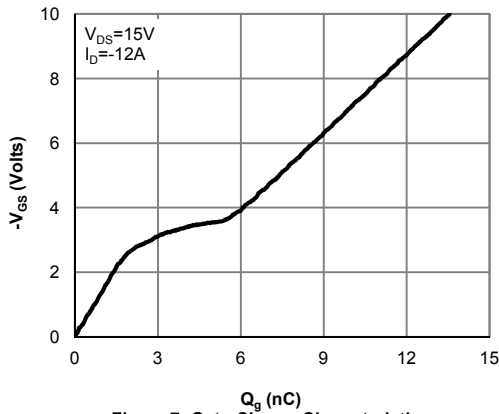


Figure 7: Gate-Charge Characteristics

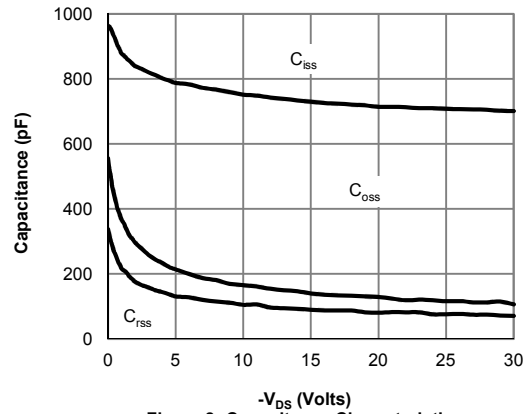


Figure 8: Capacitance Characteristics

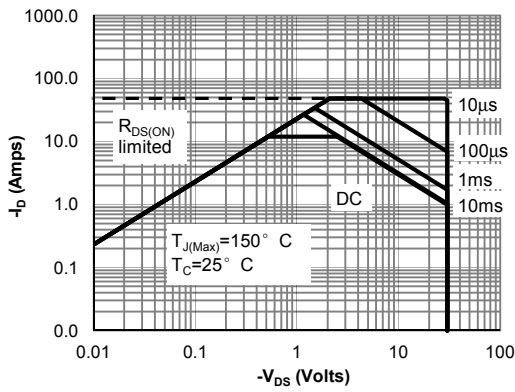


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

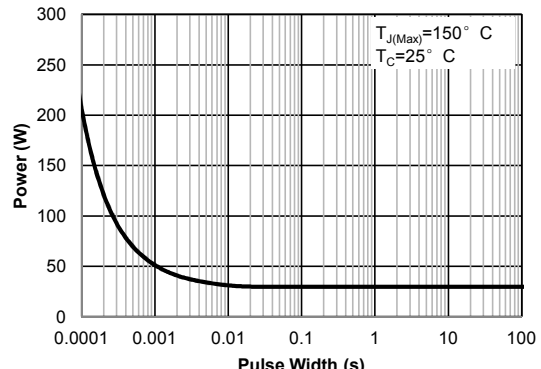


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

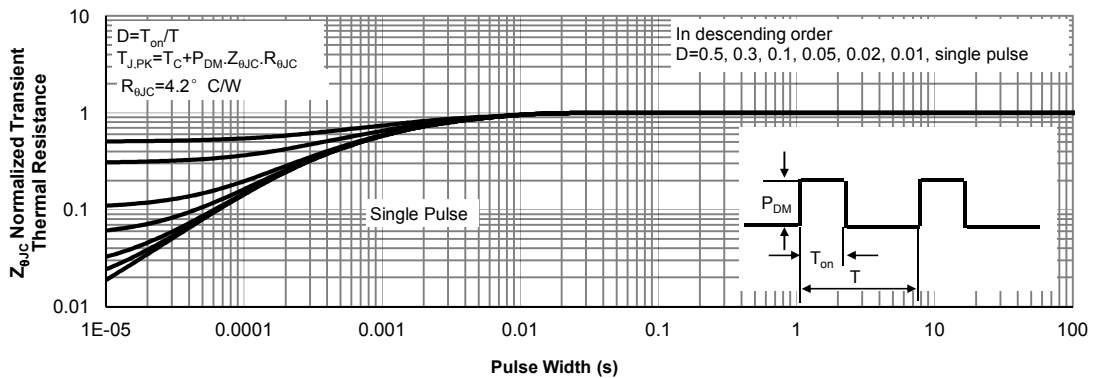


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

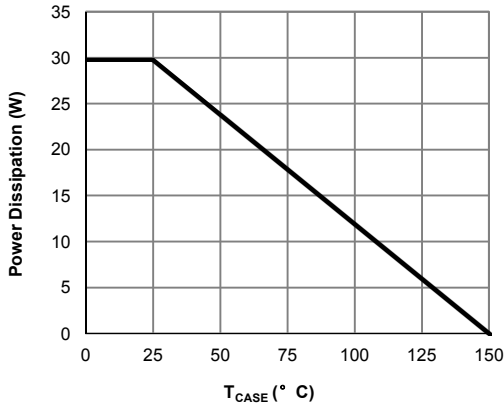


Figure 12: Power De-rating (Note F)

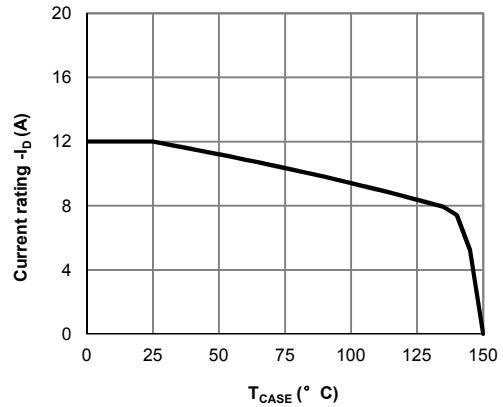


Figure 13: Current De-rating (Note F)

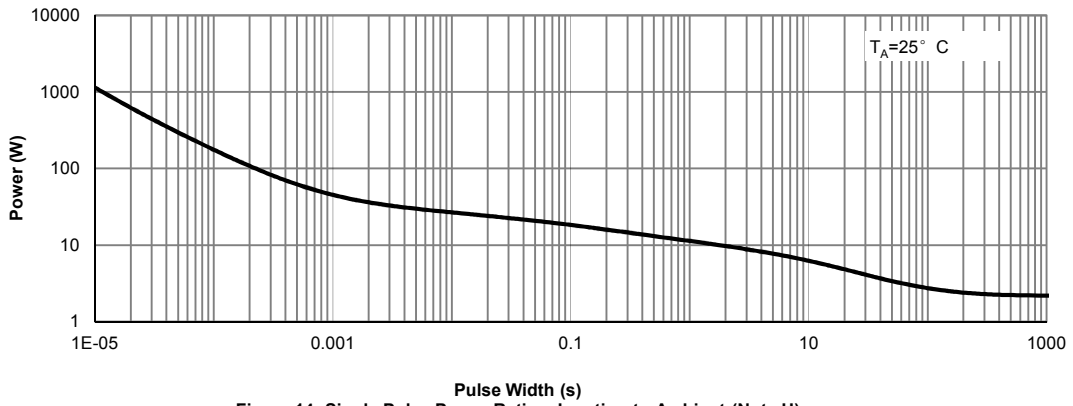


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

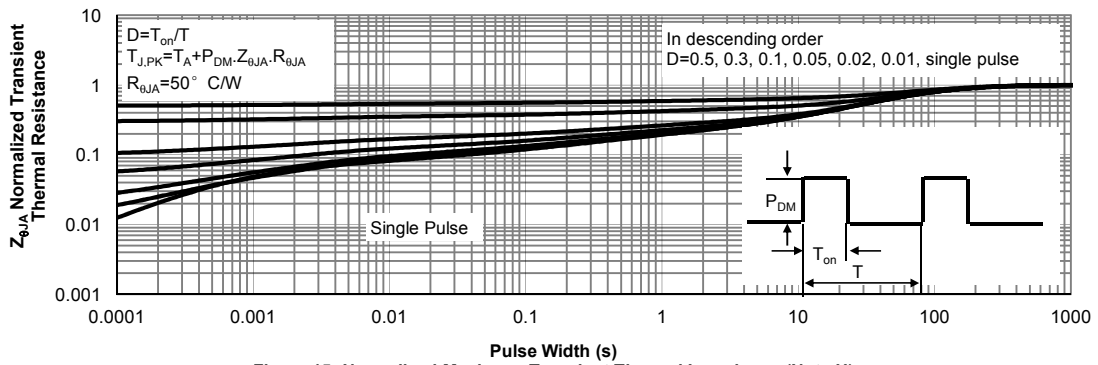


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

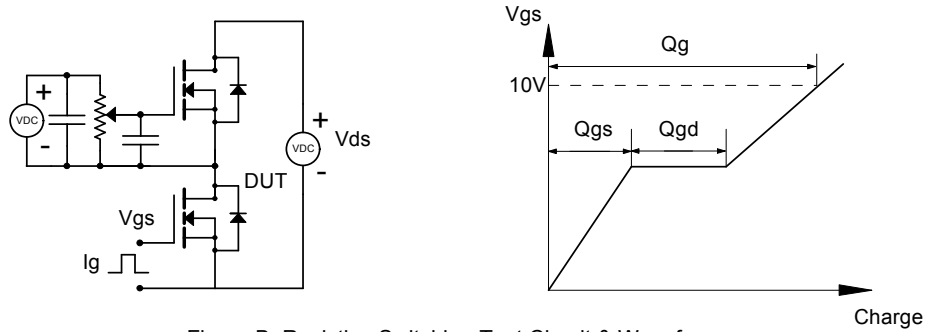


Figure B: Resistive Switching Test Circuit & Waveforms

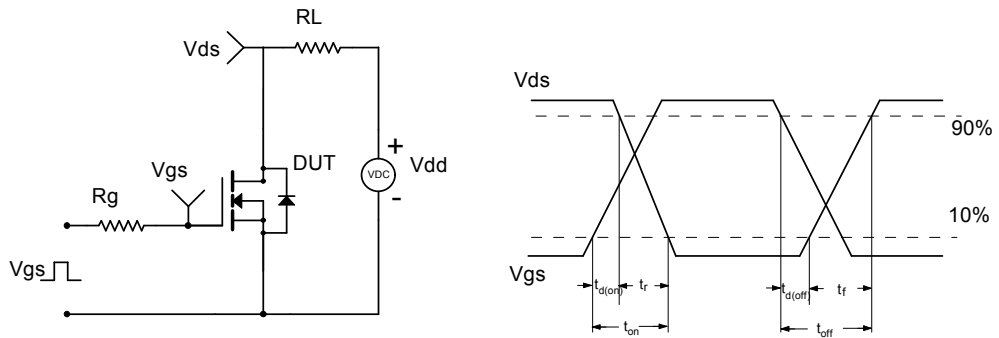


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

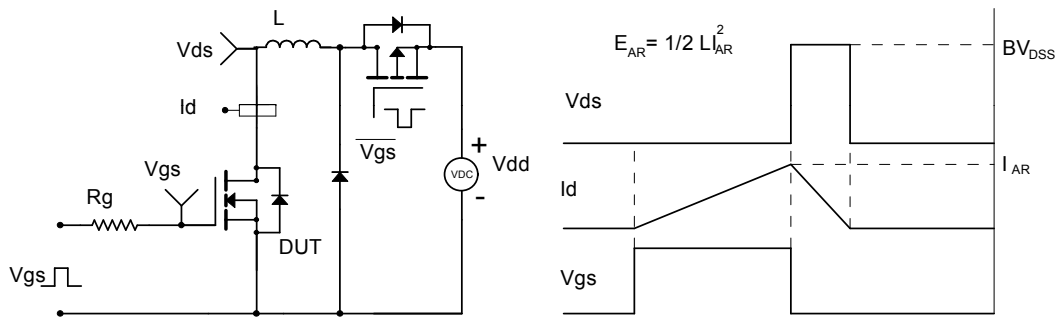
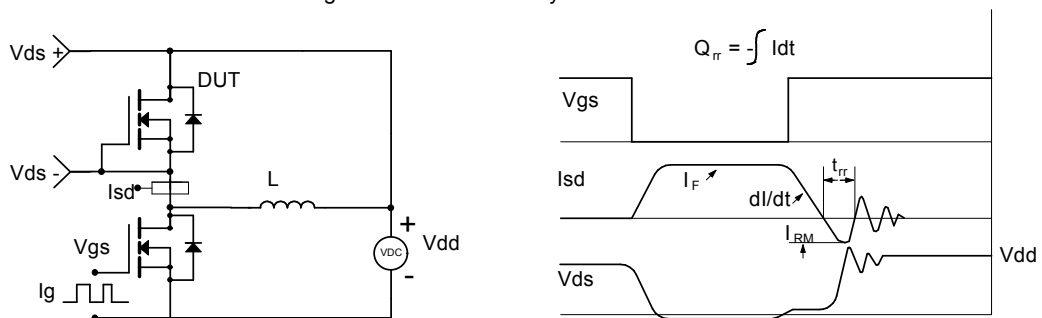
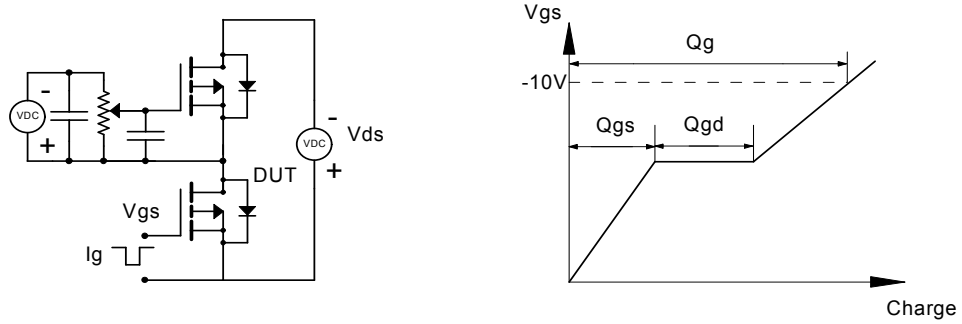


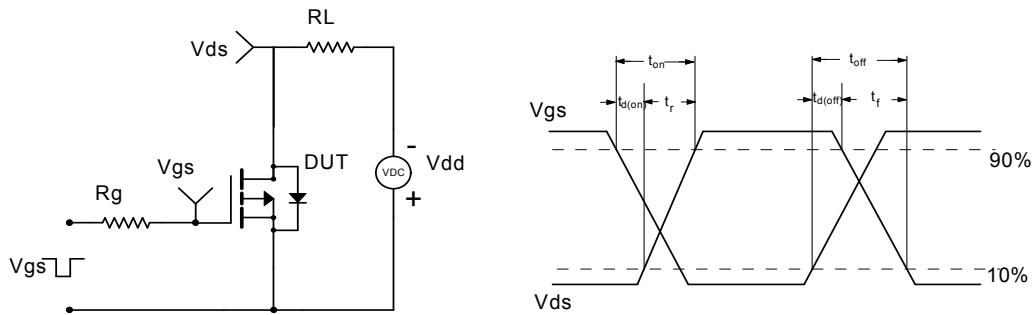
Figure D: Diode Recovery Test Circuit & Waveforms



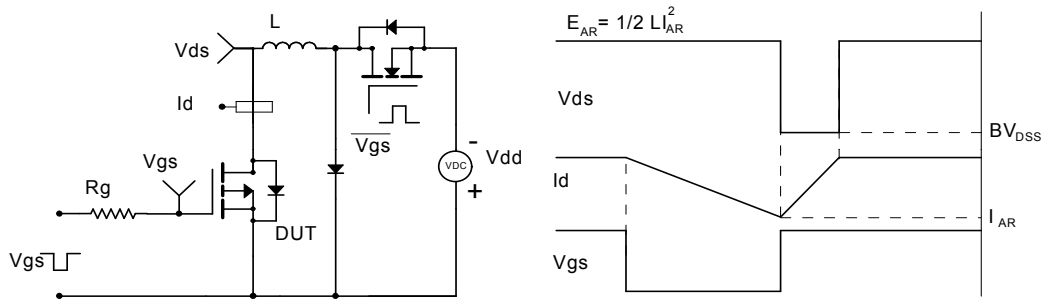
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

